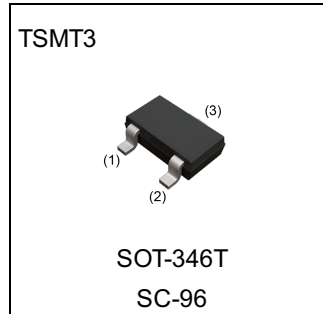


Parameter	Value
$V_{CEO}$	60V
$I_C$	2A

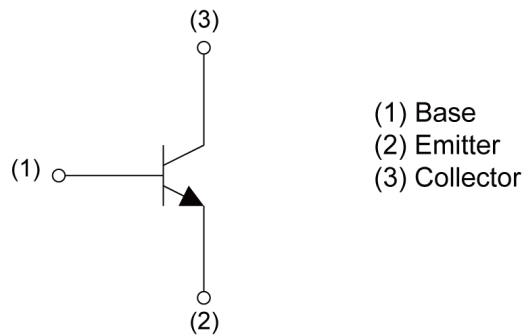
●Outline



●Features

- 1)High speed switching.  
( $t_f$ :Typ.:35ns at  $I_C=2A$ )
- 2)Low saturation voltage, typically  
(Typ.:200mV at  $I_C=1.0A$ ,  $I_B=100mA$ )
- 3)Strong discharge power for inductive load and capacitance load.
- 4)Complements the 2SA2094

●Inner circuit



●Application

LOW FREQUENCY AMPLIFIER, HIGH SPEED SWITCHING

●Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SC5866	TSMT3	2928	TL	180	8	3000	VL

**● Absolute maximum ratings** ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Values	Unit
Collector-base voltage	$V_{\text{CBO}}$	60	V
Collector-emitter voltage	$V_{\text{CEO}}$	60	V
Emitter-base voltage	$V_{\text{EBO}}$	6	V
Collector current	$I_{\text{C}}$	2	A
	$I_{\text{CP}}^{*1}$	4	A
Power dissipation	$P_{\text{D}}^{*2}$	0.5	W
Junction temperature	$T_{\text{j}}$	150	$^\circ\text{C}$
Range of storage temperature	$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

**● Electrical characteristics** ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector-base breakdown voltage	$BV_{\text{CBO}}$	$I_{\text{C}} = 100\mu\text{A}$	60	-	-	V
Collector-emitter breakdown voltage	$BV_{\text{CEO}}$	$I_{\text{C}} = 1\text{mA}$	60	-	-	V
Emitter-base breakdown voltage	$BV_{\text{EBO}}$	$I_{\text{E}} = 100\mu\text{A}$	6	-	-	V
Collector cut-off current	$I_{\text{CBO}}$	$V_{\text{CB}} = 40\text{V}$	-	-	1.0	$\mu\text{A}$
Emitter cut-off current	$I_{\text{EBO}}$	$V_{\text{EB}} = 4\text{V}$	-	-	1.0	$\mu\text{A}$
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = 1.0\text{A}, I_{\text{B}} = 100\text{mA}$	-	200	500	mV
DC current gain	$h_{\text{FE}}$	$V_{\text{CE}} = 2\text{V}, I_{\text{C}} = 100\text{mA}$	120	-	390	-
Transition frequency	$f_{\text{T}}^{*3}$	$V_{\text{CE}} = 10\text{V}, I_{\text{E}} = -100\text{mA}, f = 10\text{MHz}$	-	200	-	MHz
Output capacitance	$C_{\text{ob}}$	$V_{\text{CB}} = 10\text{V}, I_{\text{E}} = 0\text{A}, f = 1\text{MHz}$	-	10	-	pF
Turn-On time	$t_{\text{on}}^{*3}$	$I_{\text{C}} = 2\text{A}, I_{\text{B1}} = 200\text{mA}$	-	50	-	ns
Storage time	$t_{\text{stg}}^{*3}$	$I_{\text{B2}} = -200\text{mA}, V_{\text{CC}} \approx 25\text{V}$	-	120	-	ns
Fall time	$t_{\text{f}}^{*3}$	$R_{\text{L}} = 12.5\Omega$ See test circuit	-	35	-	ns

$h_{\text{FE}}$  values are classified as follows :

rank	Q	R	-	-	-
$h_{\text{FE}}$	120-270	180-390	-	-	-

\*1  $P_w = 10\text{ms}$

\*2 Each terminal mounted on a reference land.

\*3 Pulsed

● Electrical characteristic curves ( $T_a = 25^\circ\text{C}$ )

Fig.1 Ground Emitter Propagation Characteristics

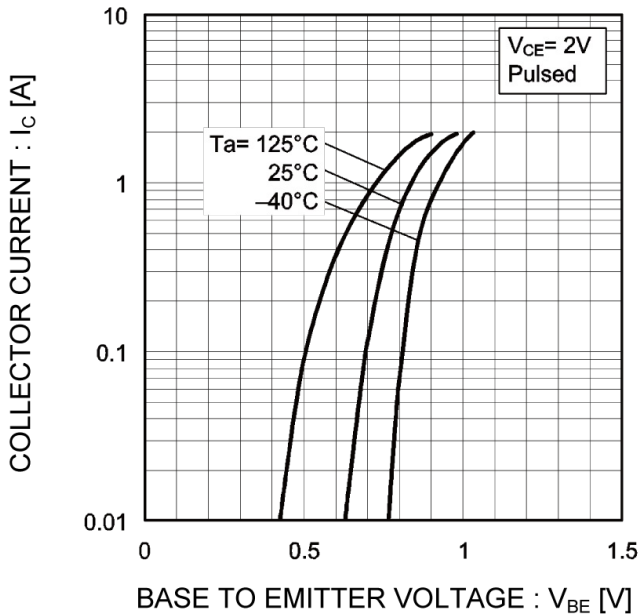


Fig.2 Typical Output Characteristics

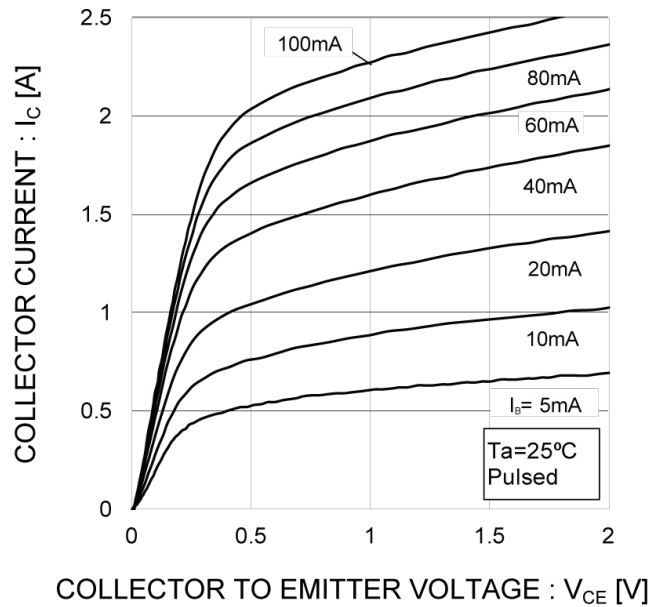


Fig.3 DC Current Gain vs. Collector Current (I)

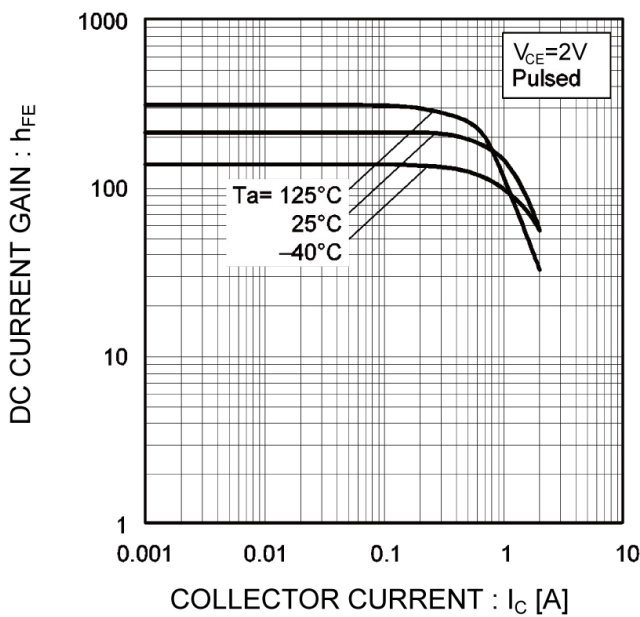
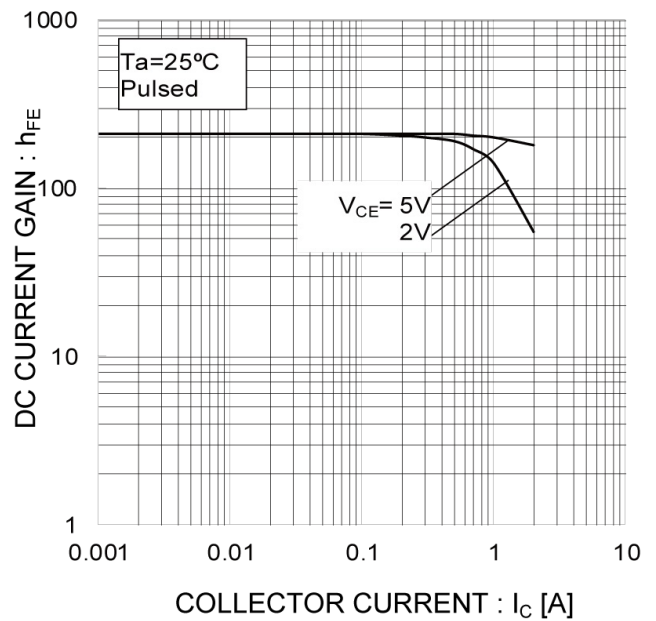


Fig.4 DC Current Gain vs. Collector Current (II)



● Electrical characteristic curves ( $T_a = 25^\circ\text{C}$ )

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

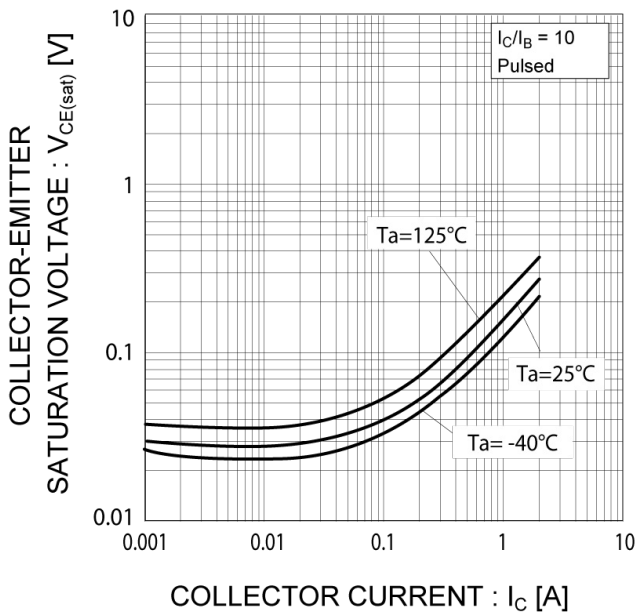


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

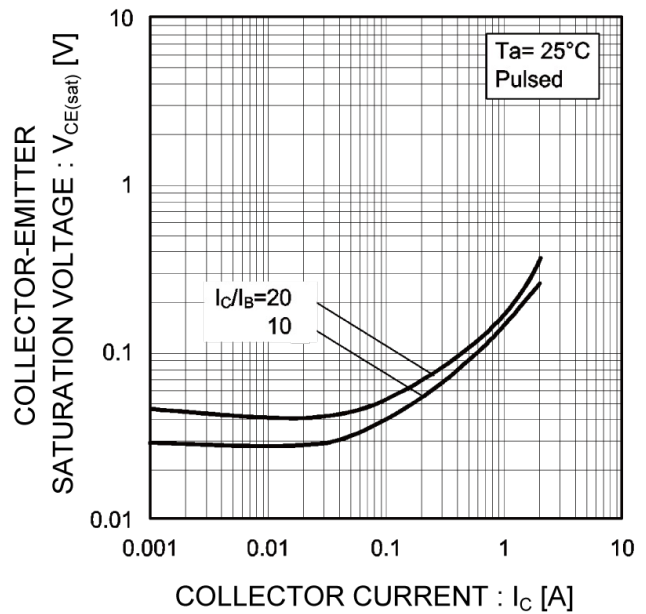


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

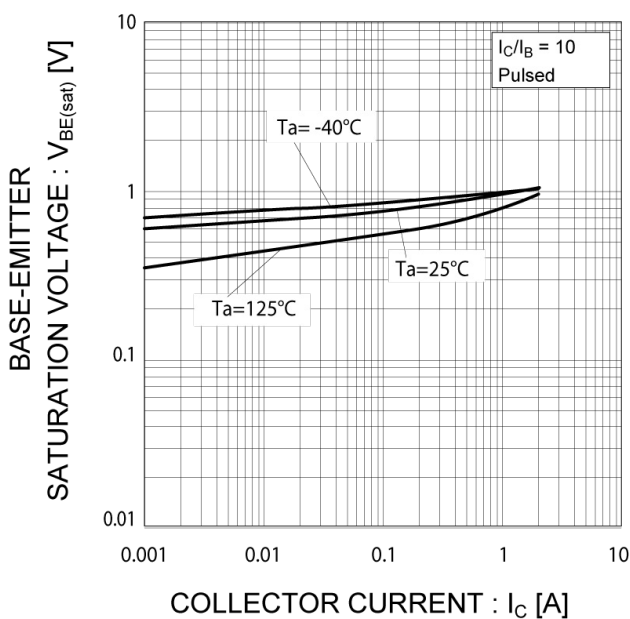
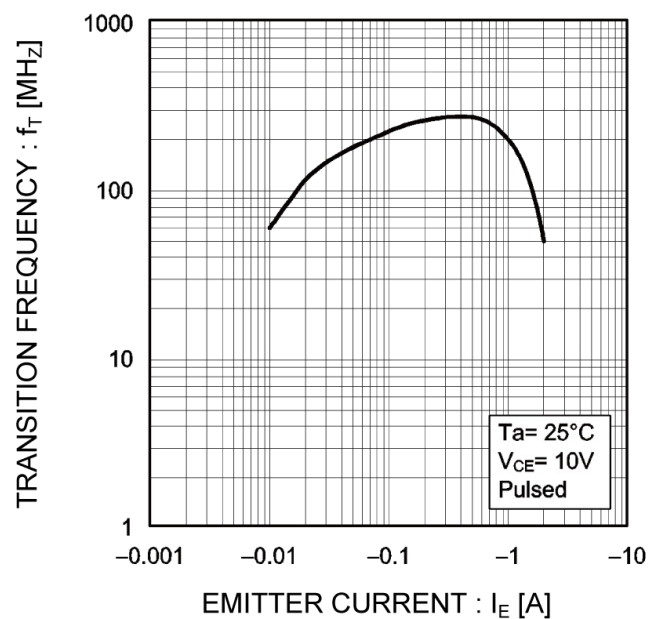


Fig.8 Gain Bandwidth Product vs. Emitter Current



●Electrical characteristic curves( $T_a = 25^\circ\text{C}$ )

Fig.9 Collector Output Capacitance vs. Collector-Base Voltage

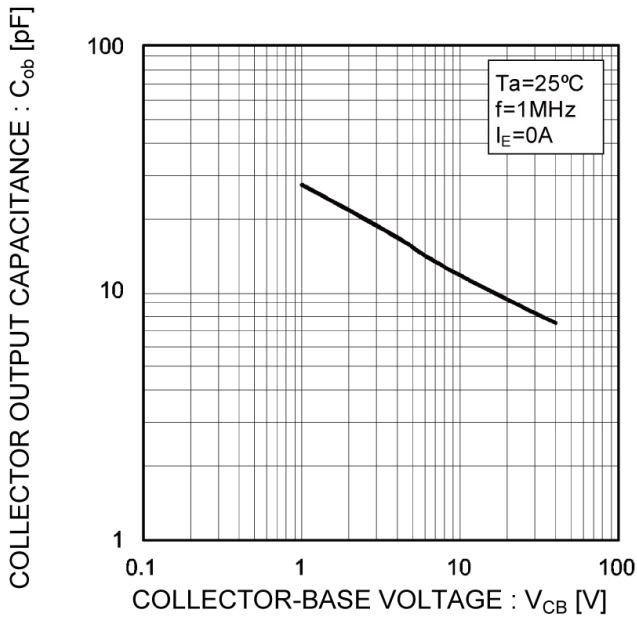
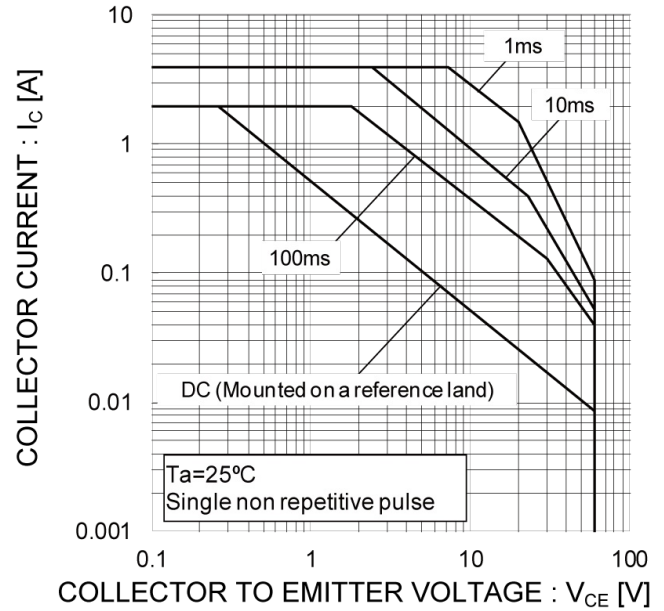
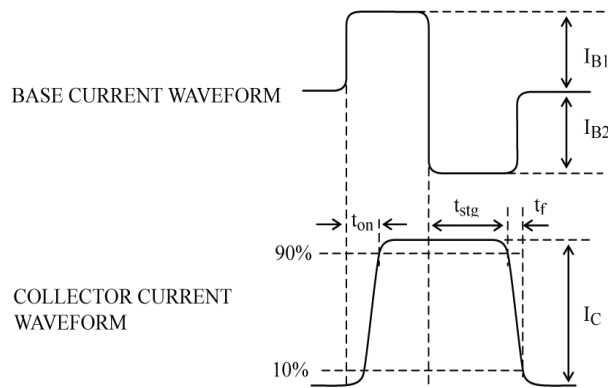
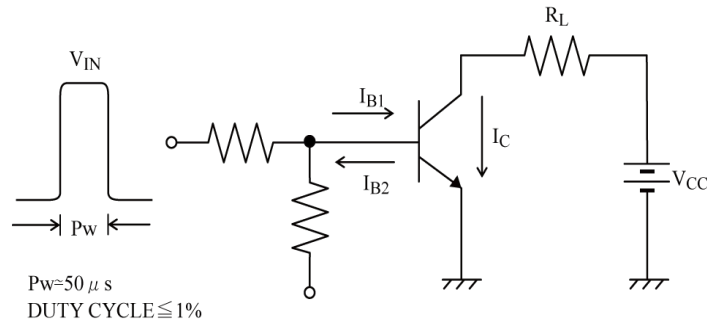


Fig.10 Safe Operating Area



SWITCHING TIME TEST CIRCUIT



●Dimensions

TSMT3



Pattern of terminal position areas  
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.00	-	0.039
A1	0.00	0.10	0.000	0.004
A2	0.75	0.95	0.030	0.037
A3	0.25		0.010	
b	0.35	0.50	0.014	0.020
c	0.10	0.26	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.010
x	-	0.20	-	0.008

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.70	-	0.028
e1	2.10		0.083	
I1	-	0.90	-	0.035

Dimension in mm/inches

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